
HRF32

Silicon Schottky Barrier Diode for High Frequency Rectifying

HITACHI

ADE-208-164B (Z)

Rev. 2

Nov. 1994

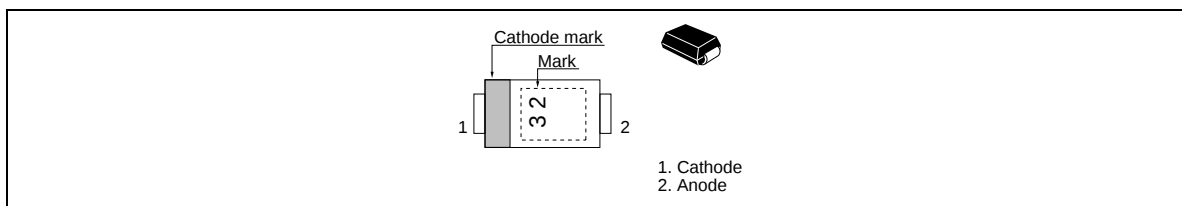
Features

- Good for high-frequency rectify for $V_R = 90V$, $I_o = 1.0A$, Output voltage = 12Vmax.
- LRP structure ensures higher reliability.

Ordering Information

Type No.	Laser Mark	Package Code
HRF32	32	LRP

Outline



Absolute Maximum Ratings ($T_a = 25^\circ C$)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	90	V
Average forward current	I_o	1.0	A
Non-Repetitive peak forward surge current	I_{FSM}^*	20	A
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{stg}	-40 to +125	$^\circ C$

Note: 10msec sine wave 1 pulse

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Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.8	V	$I_F = 1.0A$
Reverse current	I_R	—	—	1.0	mA	$V_R = 90V$

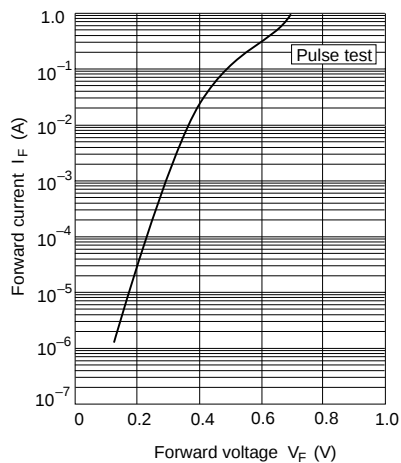


Fig.1 Forward current Vs. Forward voltage

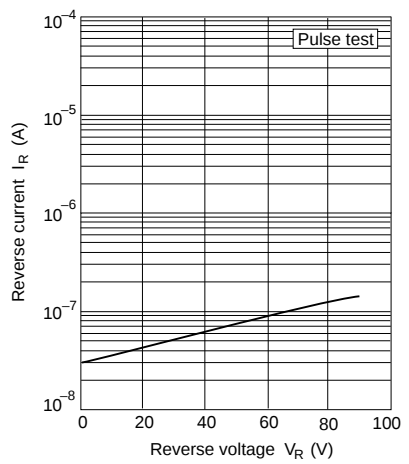


Fig.2 Reverse current Vs. Reverse voltage

Package Dimensions

